

## AMENDMENTS TO THE CLAIMS

The listing of claims will replace all prior versions, and listings, of claims in the application:

### 5 Listing of Claims:

Claims 1-6. (cancelled)

7. (previously presented): A method of making a semiconductor device  
10 comprising:

depositing a layer of oxide proximate a first surface of a semiconductor substrate;

forming a gate oxide layer on the first surface, adjacent to the deposited oxide layer;

15 after the depositing of the layer of oxide, forming a pair of active areas in the first surface, adjacent the deposited oxide layer and gate oxide layer;

forming a gate electrode by depositing a conductive layer over the gate oxide layer;

20 depositing a dielectric layer over the gate electrode, active areas, and deposited oxide layer; and

forming electrical contacts to the pair of active areas and the gate electrode.

8. (original): The method of Claim 7, further comprising thermally  
25 growing a thermal oxide layer before depositing the layer of oxide on the first surface of the semiconductor substrate.

9. (original): The method of Claim 7, wherein the semiconductor substrate is P type silicon.

10. (original): The method of Claim 7, wherein the active areas are formed  
5 by impurity implant and diffusion.

11. (original): The method of Claim 7, wherein the active areas are n doped regions.

10 12. (original): The method of Claim 7, wherein the conductive layer over the gate oxide layer is polysilicon.

13. (original): The method of Claim 7, wherein the dielectric layer is silicon dioxide.

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Claims 14-18 (cancelled)

19. (previously presented): A method comprising manufacturing a fluid ejection device by:

20 depositing a current prevention layer proximate a first surface of a semiconductor substrate; and

forming first and second field effect transistors (FETs), wherein each said FET includes a gate electrode with associated active areas formed in the first surface of the semiconductor substrate having the deposited current  
25 prevention layer thereon, wherein the current prevention layer includes a region that minimizes current flow between the active areas of the first FET with respect to the active areas of the second FET.

20. (original): The method of Claim 19, wherein the current prevention layer is a dielectric.

5 21. (original): The method of Claim 19, wherein the current prevention layer is an oxide.

22. (currently amended): A method comprising:

10 depositing a layer of oxide proximate a first surface of a semiconductor substrate;

exposing a portion of the first surface of the semiconductor substrate; and

15 forming a field effect transistor (FET) on the exposed portion of the first surface of the substrate having the deposited oxide layer, wherein the FET includes a gate electrode with associated active areas formed after the exposing the first surface of the semiconductor substrate, and wherein the active areas are is electrically isolated by the deposited layer of oxide.

23. (previously presented): A product formed by the method of Claim 22.

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24. (previously presented): A method of making a semiconductor device comprising:

depositing a layer of oxide proximate a first surface of a semiconductor substrate;

25 exposing a portion of the first surface of the semiconductor substrate;

forming a gate oxide layer on the exposed portion of the first surface, adjacent to the deposited oxide layer;

forming a pair of active areas in the exposed portion of the first surface,  
adjacent the deposited oxide layer and gate oxide layer;

forming a gate electrode by depositing a conductive layer over the gate  
oxide layer;

5        depositing a dielectric layer over the gate electrode, active areas, and  
deposited oxide layer; and

forming electrical contacts to the pair of active areas and the gate  
electrode.

10    25. (previously presented): The method of Claim 24, further comprising  
thermally growing a thermal oxide layer before depositing the layer of oxide on  
the first surface of the semiconductor substrate.

15    26. (previously presented): The method of Claim 24, wherein the  
semiconductor substrate is P type silicon.

27. (previously presented): The method of Claim 24, wherein the active  
areas are formed by impurity implant and diffusion.

20    28. (previously presented): The method of Claim 24, wherein the active  
areas are n doped regions.

29. (previously presented): The method of Claim 24, wherein the conductive  
layer over the gate oxide layer is polysilicon.

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30. (previously presented): The method of Claim 24, wherein the dielectric  
layer is silicon dioxide.

31. (previously presented): A semiconductor device produced by the method of claim 24.

5 32. (previously presented): A semiconductor device produced by the method of claim 7.

33. (previously presented): A fluid ejection device produced by the method of claim 19.

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